



ELECTRONICS, INC.
 44 FARRAND STREET
 BLOOMFIELD, NJ 07003
 (973) 748-5089
<http://www.nteinc.com>

NTE44 (NPN) & NTE45 (PNP) Silicon Complementary Transistors Dual, Bias Amp, High Gain, Low Noise, Common Base

Absolute Maximum Ratings: ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Collector-Base Voltage, V_{CBO}	100V
Collector-Emitter Voltage, V_{CEO}	100V
Emitter-Base Voltage, V_{EBO}	5V
Collector Current, I_C	100mA
Collector Power Dissipation (Per Unit), P_C	200mW
Total Power Dissipation, P_T	400mW
Junction Temperature, T_J	+125°C
Storage Temperature Range, T_{stg}	-55° to +125°C

Note 1. **NTE44** is a **discontinued** device and **no longer available**.

Electrical Characteristics: ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 100\mu\text{A}, R_{BE} = \infty$	100	-	-	V
Collector-Cutoff Current	I_{CBO}	$V_{CB} = 100\text{V}, I_E = 0$	-	-	0.1	μA
	I_{CEO}	$V_{CE} = 100\text{V}, R_{BE} = \infty$	-	-	10	μA
Emitter-Cutoff Current	I_{EBO}	$V_{EB} = 5\text{V}, I_C = 0$	-	-	0.1	μA
DC Current Gain	h_{FE}	$V_{CE} = 6\text{V}, I_C = 1\text{mA}$	400	-	800	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 10\text{mA}, I_B = 1\text{mA}$	-	-	0.3	V
Base-Emitter Voltage Differential	$V_{BE1} - V_{BE2}$	$V_{CE} = 6\text{V}, I_C = 1\text{mA}$	-	1	10	mV
Collector Current Ratio	I_{C2}/I_{C1}	$V_{CE} = 6\text{V}, I_{C1} = 1\text{mA}$	0.8	0	1.25	
Transistion Frequency	f_T	$V_{CE} = 6\text{V}, I_E = 1\text{mA}$	-	100	-	MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = 6\text{V}, I_E = 0, f = 1\text{MHz}$	-	3	-	pF
Noise Figure	NF	$V_{CE} = 6\text{V}, I_E = 0.3, f = 100\text{Hz}, R_G = 1\text{k}\Omega$	-	0.6	-	dB

